

**Amendments to the Specification**

Please amend the paragraph under the "Related Patent Data" section on page 1 as follows: •

This patent resulted from a divisional application of U.S. Patent Application Serial No. 10/323,525, filed December 18, 2002, entitled "Microelectronic Device Fabricating Method, and Method of Forming a Pair of Field Effect Transistor Gate Lines of Different Base Widths from a Common Deposited Conductive Layer", naming Alan R. Reinberg as inventor, the disclosure of which is incorporated by reference; which was a continuation application of U.S. Patent Application Serial No. ~~08/864,559~~ 09/864,559 (now U.S. Patent No. 6,509,626 B2), filed May 23, 2001, entitled "Conductive Device Components of Different Base Widths Formed from a Common Conductive Layer", naming Alan R. Reinberg as inventor, the disclosure of which is incorporated by reference; which was a divisional application of U.S. Patent Application Serial No. ~~08/579,538~~ 09/579,538 (now U.S. Patent No. 6,277,704 B1), filed May 24, 2000, entitled "Microelectronic Device Fabricating Method, Method of Forming a Pair of Conductive Device Components of Different Base Widths from a Common Deposited Conductive Layer", naming Alan R. Reinberg as inventor, the disclosure of which is incorporated by reference.